

Vanya Darakchieva

List of Publications by Year in descending order

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163
papers

4,473
citations

126858

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61
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167
all docs

167
docs citations

167
times ranked

5021
citing authors

#	ARTICLE	IF	CITATIONS
1	Ti thin films deposited by high-power impulse magnetron sputtering in an industrial system: Process parameters for a low surface roughness. Vacuum, 2022, 195, 110698. Infrared dielectric functions and Brillouin zone center phonons of $\text{Al}_{1-x}\text{Ga}_x\text{N}$ compared to AlN . Physical Review Materials, 2022, 6, 014401.	1.6	8
2	Impact of in situ NH ₃ pre-treatment of LPCVD SiN passivation on GaN HEMT performance. Semiconductor Science and Technology, 2022, 37, 035011.	0.9	10
3	Electrical Tuning of Plasmonic Conducting Polymer Nanoantennas. Advanced Materials, 2022, 34, e2107172.	11.1	32
5	Linear strain and stress potential parameters for the three fundamental band to band transitions in $\text{Al}_x\text{Ga}_{1-x}\text{N}$. Applied Physics Letters, 2022, 120, .	1.5	3
6	On the polarity determination and polarity inversion in nitrogen-polar group III-nitride layers grown on SiC. Journal of Applied Physics, 2022, 131, .	1.1	5
7	Terahertz electron paramagnetic resonance generalized spectroscopic ellipsometry: The magnetic response of the nitrogen defect in 4H-SiC. Applied Physics Letters, 2022, 120, .	1.5	8
8	Infrared-active phonon modes and static dielectric constants in $\text{Al}_{1-x}\text{Ga}_x\text{N}$ (0.18 ≤ x ≤ 0.54) alloys. Applied Physics Letters, 2022, 120, .	1.5	4
9	Mg-doping and free-hole properties of hot-wall MOCVD GaN. Journal of Applied Physics, 2022, 131, .	1.1	14
10	Epitaxial growth of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ -Ga ₂ O ₃ by hot-wall MOCVD. AIP Advances, 2022, 12, .	0.6	17
11	Enhancement of 2DEG effective mass in AlN/Al _{0.78} Ga _{0.22} N high electron mobility transistor structure determined by THz optical Hall effect. Applied Physics Letters, 2022, 120, .	1.5	3
12	Doped semiconducting polymer nanoantennas for tunable organic plasmonics. Communications Materials, 2022, 3, .	2.9	9
13	Resolving mobility anisotropy in quasi-free-standing epitaxial graphene by terahertz optical Hall effect. Carbon, 2021, 172, 248-259.	5.4	4
14	Critical View on Buffer Layer Formation and Monolayer Graphene Properties in High-Temperature Sublimation. Applied Sciences (Switzerland), 2021, 11, 1891.	1.3	3
15	Optical phonon modes, static and high-frequency dielectric constants, and effective electron mass parameter in cubic In ₂ O ₃ . Journal of Applied Physics, 2021, 129, .	1.1	11
16	Tunable Structural Color Images by UV-Exposed Patterned Conducting Polymer Nanofilms on Metal Surfaces. Advanced Materials, 2021, 33, e2102451.	11.1	34
17	Tunable Structural Color Images by UV-Exposed Patterned Conducting Polymer Nanofilms on Metal Surfaces (Adv. Mater. 33(2021)). Advanced Materials, 2021, 33, 2170261.	11.1	5
18	Thermal conductivity of ultra-wide bandgap thin layers of High Al-content AlGa _N and $\text{Al}_x\text{Ga}_{1-x}\text{N}$ -Ga ₂ O ₃ . Physica B: Condensed Matter, 2020, 579, 411810.	1.3	18

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19	N-polar AlN nucleation layers grown by hot-wall MOCVD on SiC: Effects of substrate orientation on the polarity, surface morphology and crystal quality. <i>Physica B: Condensed Matter</i> , 2020, 580, 411819.	1.3	8
20	Origin of layer decoupling in ordered multilayer graphene grown by high-temperature sublimation on C-face 4H-SiC. <i>APL Materials</i> , 2020, 8, .	2.2	4
21	Conductive polymer nanoantennas for dynamic organic plasmonics. <i>Nature Nanotechnology</i> , 2020, 15, 35-40.	15.6	70
22	Optimization of GaN Nanowires Reformation Process by Metalorganic Chemical Vapor Deposition for Device-Quality GaN Templates. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900581.	0.7	5
23	Morphology of Thin Films of Aromatic Ellagic Acid and Its Hydrogen Bonding Interactions. <i>Journal of Physical Chemistry C</i> , 2020, 124, 16381-16390.	1.5	4
24	Brillouin zone center phonon modes in ZnGa ₂ O ₄ . <i>Applied Physics Letters</i> , 2020, 117, .	1.5	5
25	Tunable cavity-enhanced terahertz frequency-domain optical Hall effect. <i>Review of Scientific Instruments</i> , 2020, 91, 083903.	0.6	11
26	Strain and stress relationships for optical phonon modes in monoclinic crystals with Γ^2 as an example. <i>Physical Review B</i> , 2020, 102, .	1.1	18
27	Comment on "Characteristics of Multi-photon Absorption in a Γ^2 -Ga ₂ O ₃ Single Crystal". <i>J. Phys. Soc. Jpn.</i> 88, 113701 (2019)]. <i>Journal of the Physical Society of Japan</i> , 2020, 89, 036001.	0.7	0
28	Infrared active phonons in monoclinic lutetium oxyorthosilicate. <i>Journal of Applied Physics</i> , 2020, 127, .	1.1	6
29	How Much Oxygen Can a MXene Surface Take Before It Breaks?. <i>Advanced Functional Materials</i> , 2020, 30, 1909005.	7.8	111
30	Phonon-boundary scattering and thermal transport in Al _x Ga _{1-x} N: Effect of layer thickness. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	11
31	The anisotropic quasi-static permittivity of single-crystal Γ^2 -Ga ₂ O ₃ measured by terahertz spectroscopy. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	27
32	Phonon Properties. <i>Springer Series in Materials Science</i> , 2020, , 501-534.	0.4	1
33	Electronic and optical characterization of 2D Ti ₂ C and Nb ₂ C (MXene) thin films. <i>Journal of Physics Condensed Matter</i> , 2019, 31, 165301.	0.7	74
34	Dielectric function tensor (1.5 eV to 9.0 eV), anisotropy, and band to band transitions of monoclinic Γ^2 -(Al _x Ga _{1-x}) ₂ O ₃ (x = 0.21) films. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	25
35	Lattice dynamics of orthorhombic NdGaO ₃ . <i>Physical Review B</i> , 2019, 99, .		
36	On the anomalous optical conductivity dispersion of electrically conducting polymers: ultra-wide spectral range ellipsometry combined with a Drude-Lorentz model. <i>Journal of Materials Chemistry C</i> , 2019, 7, 4350-4362.	2.7	36

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37	Longitudinal phonon plasmon mode coupling in $\text{In}_x\text{Ga}_{1-x}\text{N}$ -Ga ₂ O ₃ . Applied Physics Letters, 2019, 114, .	1.5	21
38	Terahertz optical properties of polymethacrylates after thermal annealing. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2019, 37, 062924.	0.6	3
39	Phonon order and reststrahlen bands of polar vibrations in crystals with monoclinic symmetry. Physical Review B, 2019, 99, .	1.1	13
40	Recombination processes in Mg doped wurtzite InN films with p- and n-type conductivity. AIP Advances, 2019, 9, 015114.	0.6	1
41	2D Transition Metal Carbides (MXenes) for Carbon Capture. Advanced Materials, 2019, 31, e1805472.	11.1	184
42	Electron effective mass in In _{0.33} Ga _{0.67} N determined by mid-infrared optical Hall effect. Applied Physics Letters, 2018, 112, .	1.5	6
43	Tailoring Structure, Composition, and Energy Storage Properties of MXenes from Selective Etching of In-plane, Chemically Ordered MAX Phases. Small, 2018, 14, e1703676.	5.2	174
44	Electron effective mass in Sn-doped monoclinic single crystal In_2O_3 -gallium oxide determined by mid-infrared optical Hall effect. Applied Physics Letters, 2018, 112, .	1.5	43
45	Advanced Terahertz Frequency-Domain Ellipsometry Instrumentation for <i>In Situ</i> and <i>Ex Situ</i> Applications. IEEE Transactions on Terahertz Science and Technology, 2018, 8, 257-270.	2.0	42
46	On the organization and thermal behavior of functional groups on Ti ₃ C ₂ MXene surfaces in vacuum. 2D Materials, 2018, 5, 015002.	2.0	219
47	Strong Plasmon-Exciton Coupling with Directional Absorption Features in Optically Thin Hybrid Nanohole Metasurfaces. ACS Photonics, 2018, 5, 4046-4055.	3.2	37
48	Multi-scale investigation of interface properties, stacking order and decoupling of few layer graphene on C-face 4H-SiC. Carbon, 2017, 116, 722-732.	5.4	23
49	Infrared dielectric functions, phonon modes, and free-charge carrier properties of high-Al-content Al _x Ga _{1-x} N alloys determined by mid infrared spectroscopic ellipsometry and optical Hall effect. Journal of Applied Physics, 2017, 121, .	1.1	14
50	In-situ terahertz optical Hall effect measurements of ambient effects on free charge carrier properties of epitaxial graphene. Scientific Reports, 2017, 7, 5151.	1.6	23
51	Cavity-enhanced optical Hall effect in epitaxial graphene detected at terahertz frequencies. Applied Surface Science, 2017, 421, 357-360.	3.1	8
52	Band-to-band transitions, selection rules, effective mass, and excitonic contributions in monoclinic $\text{In}_x\text{Ga}_{1-x}\text{N}$ alloys determined by mid infrared spectroscopic ellipsometry and optical Hall effect. Physical Review B, 2017, 96, .	1.1	17
53	Decoupling and ordering of multilayer graphene on C-face 3C-SiC(111). Applied Physics Letters, 2016, 109, .	1.5	10
54	Optical Hall effect model description: tutorial. Journal of the Optical Society of America A: Optics and Image Science, and Vision, 2016, 33, 1553.	0.8	40

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55	Anisotropy, phonon modes, and free charge carrier parameters in monoclinic α -gallium oxide single crystals. <i>Physical Review B</i> , 2016, 93, .	1.1	147
56	Properties of two-dimensional electron gas in AlGaIn/GaN HEMT structures determined by cavity-enhanced THz optical Hall effect. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 369-373.	0.8	15
57	Infrared dielectric functions and optical phonons of wurtzite $\text{Al}_x\text{In}_{1-x}\text{N}$ ($0 \leq x \leq 1$). <i>Journal of Applied Physics</i> , 48, 415102.		
58	Atomic layer deposition of Al_2O_3 on NF_3 -pre-treated graphene. , 2015, , .		2
59	Structural properties and dielectric function of graphene grown by high-temperature sublimation on 4H-SiC(000-1). <i>Journal of Applied Physics</i> , 2015, 117, .	1.1	16
60	Cavity-enhanced optical Hall effect in two-dimensional free charge carrier gases detected at terahertz frequencies. <i>Optics Letters</i> , 2015, 40, 2688.	1.7	19
61	Correlation between switching to n-type conductivity and structural defects in highly Mg-doped InN. <i>Applied Physics Letters</i> , 2015, 106, 232102.	1.5	7
62	Stress evolution during growth of GaN (0001)/ Al_2O_3 (0001) by reactive dc magnetron sputter epitaxy. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 145301.	1.3	11
63	Effect of Mg doping on the structural and free-charge carrier properties of InN films. <i>Journal of Applied Physics</i> , 2014, 115, 163504.	1.1	16
64	Assessing structural, free-charge carrier, and phonon properties of mixed-phase epitaxial films: The case of InN. <i>Physical Review B</i> , 2014, 90, .	1.1	15
65	Free-charge carrier parameters of n-type, p-type and compensated InN:Mg determined by infrared spectroscopic ellipsometry. <i>Thin Solid Films</i> , 2014, 571, 384-388.	0.8	4
66	Morphological and electronic properties of epitaxial graphene on SiC. <i>Physica B: Condensed Matter</i> , 2014, 439, 54-59.	1.3	29
67	Infrared to vacuum-ultraviolet ellipsometry and optical Hall-effect study of free-charge carrier parameters in Mg-doped InN. <i>Journal of Applied Physics</i> , 2013, 113, .	1.1	22
68	Structure and properties of phosphorus-carbide thin solid films. <i>Thin Solid Films</i> , 2013, 548, 247-254.	0.8	17
69	Large-area microfocal spectroscopic ellipsometry mapping of thickness and electronic properties of epitaxial graphene on Si- and C-face of 3C-SiC(111). <i>Applied Physics Letters</i> , 2013, 102, .	1.5	28
70	(Invited) Challenges of Graphene Growth on Silicon Carbide. <i>ECS Transactions</i> , 2013, 53, 9-16.	0.3	4
71	Polarization Selection Rules for Inter-Landau-Level Transitions in Epitaxial Graphene Revealed by the Infrared Optical Hall Effect. <i>Physical Review Letters</i> , 2013, 111, 077402.	2.9	18
72	Electron effective mass in $\text{Al}_{0.72}\text{Ga}_{0.28}\text{N}$ alloys determined by mid-infrared optical Hall effect. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	30

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73	Bandgap Engineering and Optical Constants of YxAl1-xN Alloys. Japanese Journal of Applied Physics, 2013, 52, 08JM02.	0.8	11
74	Infrared ellipsometry and near-infrared-to-vacuum-ultraviolet ellipsometry study of free-charge carrier properties in In-polar p-type InN. Materials Research Society Symposia Proceedings, 2012, 1396, .	0.1	0
75	Direct graphene growth on Co ₃ O ₄ (111) by molecular beam epitaxy. Journal of Physics Condensed Matter, 2012, 24, 072201.	0.7	18
76	Spectroscopic Mapping Ellipsometry of Graphene Grown on 3C SiC. Materials Research Society Symposia Proceedings, 2012, 1407, 99.	0.1	1
77	Enhanced dynamic annealing and optical activation of Eu implanted a-plane GaN. Europhysics Letters, 2012, 97, 68004.	0.7	15
78	Temperature dependent effective mass in AlGaIn/GaN high electron mobility transistor structures. Applied Physics Letters, 2012, 101, .	1.5	44
79	Visible to vacuum ultraviolet dielectric functions of epitaxial graphene on 3C and 4H SiC polytypes determined by spectroscopic ellipsometry. Applied Physics Letters, 2012, 101, .	1.5	33
80	Elastic constants, composition, and piezoelectric polarization in In _x Al _{1-x} N: P. From <i>ab initio</i> calculations to experimental implications for the applicability of Vegard's rule. $\langle i \rangle \langle j \rangle \langle k \rangle \langle l \rangle \langle m \rangle \langle n \rangle \langle o \rangle \langle p \rangle \langle q \rangle \langle r \rangle \langle s \rangle \langle t \rangle \langle u \rangle \langle v \rangle \langle w \rangle \langle x \rangle \langle y \rangle \langle z \rangle$	1.1	31
81	Y _x Al _{1-x} N thin films. Journal Physics D: Applied Physics, 2012, 45, 422001.	1.3	42
82	Unintentional incorporation of H and related structural and free electron properties of c-plane and a-plane InN. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 91-94.	0.8	4
83	Two-domain formation during the epitaxial growth of GaN (0001) on c-plane Al ₂ O ₃ (0001) by high power impulse magnetron sputtering. Journal of Applied Physics, 2011, 110, .	1.1	18
84	Standard free composition measurements of Al _x In _{1-x} N by low-loss electron energy loss spectroscopy. Physica Status Solidi - Rapid Research Letters, 2011, 5, 50-52.	1.2	15
85	Epitaxial CVD growth of sp ² -hybridized boron nitride using aluminum nitride as buffer layer. Physica Status Solidi - Rapid Research Letters, 2011, 5, 397-399.	1.2	44
86	Free electron properties and hydrogen in InN grown by MOVPE. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1179-1182.	0.8	9
87	Optical properties of InN/In _{0.73} Ga _{0.27} N multiple quantum wells studied by spectroscopic ellipsometry. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1629-1632.	0.8	1
88	Optical properties of GaAs _{0.9-x} N _x Sb _{0.1} alloy films studied by spectroscopic ellipsometry. Thin Solid Films, 2011, 519, 2838-2842.	0.8	4
89	A Double Scattering Analytical Model For Elastic Recoil Detection Analysis. , 2011, , .		1
90	Unintentional incorporation of hydrogen in wurtzite InN with different surface orientations. Journal of Applied Physics, 2011, 110, .	1.1	3

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91	Hydrogen In Group-III Nitrides: An Ion Beam Analysis Study. , 2011, , .		1
92	Al _{1-x} In _x N/GaN bilayers: Structure, morphology, and optical properties. Physica Status Solidi (B): Basic Research, 2010, 247, 1740-1746.	0.7	10
93	Hydrogen in InN: A ubiquitous phenomenon in molecular beam epitaxy grown material. Applied Physics Letters, 2010, 96, .	1.5	36
94	Effect of nitrogen on the GaAs _{0.9} N _x Sb _{0.1} dielectric function from the near-infrared to the ultraviolet. Applied Physics Letters, 2010, 97, 201903.	1.5	17
95	Structural anisotropy of nonpolar and semipolar InN epitaxial layers. Journal of Applied Physics, 2010, 108, .	1.1	21
96	Electron accumulation at nonpolar and semipolar surfaces of wurtzite InN from generalized infrared ellipsometry. Applied Physics Letters, 2009, 95, 202103.	1.5	24
97	Europium doping of zincblende GaN by ion implantation. Journal of Applied Physics, 2009, 105, 113507.	1.1	8
98	DAP emission band in a carbon doped (1101)GaN grown on (001)Si substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S772.	0.8	2
99	Role of impurities and dislocations for the unintentional n-type conductivity in InN. Physica B: Condensed Matter, 2009, 404, 4476-4481.	1.3	15
100	Free electron behavior in InN: On the role of dislocations and surface electron accumulation. Applied Physics Letters, 2009, 94, 022109.	1.5	41
101	Optical Hall Effect in Hexagonal InN. Journal of Electronic Materials, 2008, 37, 611-615.	1.0	39
102	Strain and compositional analyses of Al _{1-x} In _x N films grown by MOVPE: impact on the applicability of Vegard's rule. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1859-1862.	0.8	3
103	Infrared generalized ellipsometry on nonpolar and superlattice group-III nitride films: strain and phonon anisotropy. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 905-913.	0.8	11
104	Lattice parameters of bulk GaN fabricated by halide vapor phase epitaxy. Journal of Crystal Growth, 2008, 310, 959-965.	0.7	19
105	Very high crystalline quality of thick 4H-SiC epilayers grown from methyltrichlorosilane (MTS). Physica Status Solidi - Rapid Research Letters, 2008, 2, 188-190.	1.2	24
106	Unravelling the free electron behavior in InN. Optoelectronic and Microelectronic Materials and Devices (COMMAD), Conference on, 2008, , .	0.0	0
107	Two-dimensional electron gas density in Al _{1-x} In _x N/AlN/GaN heterostructures (0.03% x 0.23). Journal of Applied Physics, 2008, 103, .	1.1	154
108	Lattice parameters, deviations from Vegard's rule, and E2 phonons in InAlN. Applied Physics Letters, 2008, 93, .	1.5	44

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109	Effects of strain and composition on the lattice parameters and applicability of Vegard's rule in Al-rich Al _{1-x} In _x N films grown on sapphire. <i>Journal of Applied Physics</i> , 2008, 103, .	1.1	54
110	On the lattice parameters of GaN. <i>Applied Physics Letters</i> , 2007, 91, .	1.5	101
111	Anisotropic strain and phonon deformation potentials in GaN. <i>Physical Review B</i> , 2007, 75, .	1.1	99
112	Very high epitaxial growth rate of SiC using MTS as chloride-based precursor. <i>Surface and Coatings Technology</i> , 2007, 201, 8931-8934.	2.2	9
113	Effect of anisotropic strain on phonons in a-plane and c-plane GaN layers. <i>Journal of Crystal Growth</i> , 2007, 300, 233-238.	0.7	10
114	Very high growth rate of 4H-SiC epilayers using the chlorinated precursor methyltrichlorosilane (MTS). <i>Journal of Crystal Growth</i> , 2007, 307, 334-340.	0.7	83
115	Phonons in strained AlGa _n /Ga _n superlattices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 170-174.	0.8	5
116	Effect of high-temperature annealing on the residual strain and bending of freestanding GaN films grown by hydride vapor phase epitaxy. <i>Applied Physics Letters</i> , 2006, 88, 141909.	1.5	30
117	Bending in HVPE GaN free-standing films: effects of laser lift-off, polishing and high-pressure annealing. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1475-1478.	0.8	3
118	Anisotropy of the Γ^c -point effective mass and mobility in hexagonal InN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 1854-1857.	0.8	36
119	Assessment of phonon mode characteristics via infrared spectroscopic ellipsometry on a-plane GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 1594-1598.	0.7	4
120	Strain-free Low-defect-density Bulk GaN with Nonpolar Orientations. <i>Materials Research Society Symposia Proceedings</i> , 2006, 955, 1.	0.1	0
121	High-quality bulk a-plane GaN sliced from boules in comparison to heteroepitaxially grown thick films on r-plane sapphire. <i>Applied Physics Letters</i> , 2006, 89, 051914.	1.5	78
122	Properties of nonpolar a-plane GaN films grown by HVPE with AlN buffers. <i>Journal of Crystal Growth</i> , 2005, 281, 55-61.	0.7	66
123	Structural characteristics and lattice parameters of hydride vapor phase epitaxial GaN free-standing quasisubstrates. <i>Journal of Applied Physics</i> , 2005, 97, 013517.	1.1	32
124	Photoluminescence of GaN/AlN superlattices grown by MOCVD. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 2345-2348.	0.8	9
125	Nonpolar a-plane HVPE GaN: growth and in-plane anisotropic properties. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 2027-2031.	0.8	12
126	Phonon mode behavior in strained wurtzite AlN _{1-x} Ga _x N superlattices. <i>Physical Review B</i> , 2005, 71, .	1.1	38

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127	Strain-related structural and vibrational properties of thin epitaxial AlN layers. <i>Physical Review B</i> , 2004, 70, .	1.1	59
128	Deformation potentials of the E1(TO) and E2 modes of InN. <i>Applied Physics Letters</i> , 2004, 84, 3636-3638.	1.5	47
129	High pressure annealing of HVPE GaN free-standing films: redistribution of defects and stress. <i>Materials Research Society Symposia Proceedings</i> , 2004, 831, 49.	0.1	1
130	Infrared ellipsometry and Raman studies of hexagonal InN films: correlation between strain and vibrational properties. <i>Superlattices and Microstructures</i> , 2004, 36, 573-580.	1.4	16
131	Hydride vapor-phase epitaxial GaN thick films for quasi-substrate applications: Strain distribution and wafer bending. <i>Journal of Electronic Materials</i> , 2004, 33, 389-394.	1.0	20
132	Polar and nonpolar GaN grown by HVPE: Preferable substrates for nitride-based emitting devices. <i>Physica Status Solidi A</i> , 2004, 201, 2265-2270.	1.7	16
133	Optical investigation of AlGaIn/GaN quantum wells and superlattices. <i>Physica Status Solidi A</i> , 2004, 201, 2251-2258.	1.7	1
134	Grazing incident asymmetric X-ray diffraction of $\hat{\Gamma}^2$ -FeSi ₂ layers, produced by ion beam synthesis. <i>Vacuum</i> , 2004, 76, 277-280.	1.6	3
135	Characterization of mass-transport grown GaN by hydride vapour-phase epitaxy. <i>Journal of Crystal Growth</i> , 2004, 273, 118-128.	0.7	5
136	Generalized infrared ellipsometry study of thin epitaxial AlN layers with complex strain behavior. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 416-420.	1.3	3
137	Residual strain in HVPE GaN free-standing and re-grown homoepitaxial layers. <i>Physica Status Solidi A</i> , 2003, 195, 516-522.	1.7	18
138	Growth of GaN on a-plane sapphire: in-plane epitaxial relationships and lattice parameters. <i>Physica Status Solidi (B): Basic Research</i> , 2003, 240, 318-321.	0.7	16
139	Phonons and free-carrier properties of binary, ternary, and quaternary group-III nitride layers measured by Infrared Spectroscopic Ellipsometry. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 1750-1769.	0.8	16
140	Optical properties of undoped AlN/GaN superlattices grown by metalorganic vapor phase epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 2614-2617.	0.8	4
141	Free-Standing HVPE-GaN Quasi-Substrates: Impurity and Strain Distributions. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 209-213.	0.8	9
142	In-plane epitaxial relationships between a-plane sapphire substrates and GaN layers grown by different techniques. <i>Journal of Crystal Growth</i> , 2003, 257, 1-6.	0.7	7
143	Infrared dielectric functions and phonon modes of high-quality ZnO films. <i>Journal of Applied Physics</i> , 2003, 93, 126-133.	1.1	590
144	Lattice parameters of GaN layers grown on a-plane sapphire: Effect of in-plane strain anisotropy. <i>Applied Physics Letters</i> , 2003, 82, 703-705.	1.5	39

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145	Strain evolution and phonons in AlN/GaN superlattices. Materials Research Society Symposia Proceedings, 2003, 798, 610.	0.1	0
146	Photoluminescence in n-doped In _{0.1} Ga _{0.9} N/In _{0.01} Ga _{0.99} N multiple quantum wells. MRS Internet Journal of Nitride Semiconductor Research, 2002, 7, 1.	1.0	10
147	Deformation potentials of the E ₁ (TO) mode in AlN. Applied Physics Letters, 2002, 80, 2302-2304.	1.5	32
148	Anisotropy of the In-Plane Strain in GaN Grown on A-Plane Sapphire. Physica Status Solidi (B): Basic Research, 2002, 234, 892-896.	0.7	5
149	Strain Evolution in High Temperature AlN Buffer Layers for HVPE-GaN Growth. Physica Status Solidi A, 2002, 190, 59-64.	1.7	7
150	Influence of grain size on the optical conductivity of $\hat{\Gamma}^2$ -FeSi ₂ layers. Vacuum, 2002, 69, 425-429.	1.6	16
151	Effect of rapid thermal annealing on the structure of ion beam synthesized $\hat{\Gamma}^2$ -FeSi ₂ . Vacuum, 2002, 69, 449-454.	1.6	1
152	Growth and separation related properties of HVPE-GaN free-standing films. Journal of Crystal Growth, 2002, 246, 207-214.	0.7	27
153	Anisotropy of the In-Plane Strain in GaN Grown on A-Plane Sapphire. , 2002, 234, 892.		1
154	Strain Evolution in High Temperature AlN Buffer Layers for HVPE-GaN Growth. Physica Status Solidi A, 2002, 190, 59.	1.7	1
155	Defect Reduction in HVPE Growth of GaN and Related Optical Spectra. Physica Status Solidi A, 2001, 183, 197-203.	1.7	10
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